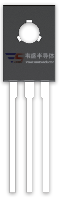
3DA882 TRANSISTOR (NPN)

FEATURES

- Low Speed Switching
- Complement to 3CA772


TO-126

1.EMITTER

2.COLLECTOR

3.BASE

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
3DA882	TO-126	Bulk	200pcs/Bag
3DA882-TU	TO-126	Tube	60pcs/Tube

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	3	A
P_C	Collector Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	100	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=40V,I_E=0			10	μA
Collector cut-off current	I_{CEO}	V_{CE}=30V,I_B=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=6V,I_C=0			10	μA
DC current gain	h_{FE}^{*}	V_{CE}=2V, I_C=1A	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}^{*}$	I_C=2A,I_B=0.2A			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=2A,I_B=0.2A			1.5	V
Transition frequency	f_T	V_{CE}=5V,I_C=0.1A, f=10MHz	50			MHz

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.

CLASSIFICATION OF h_{FE}

RANK	R	O	Y	GR
RANGE	60-120	100-200	160-320	200-400